

A6
Covell

depositing a resist over the insulating layer first regions;
depositing a second conductive material within the insulating layer second region
trenches;
removing the resist;
depositing a thin dielectric layer over the insulating layer first region within the first
region trenches; and
depositing a third conductive material over the thin dielectric layer within the first
region trenches.

12. (Amended) A method of fabricating a vertical metal-insulator-metal capacitor (MIMCap),
comprising:

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providing a wafer having a workpiece;
depositing an inter-level dielectric over the workpiece;
patterning the inter-level dielectric with a plurality of trenches, the inter-level
dielectric comprising at least one first region and at least one second region, the first region
comprising trenches for at least one MIMCap, the second region comprising trenches for a plurality
of conductive lines;

depositing a conductive liner over the inter-level dielectric within the trenches;
depositing a seed layer over the conductive liner;
depositing a resist over the seed layer;
removing the resist over the seed layer in the inter-level dielectric second regions,
leaving resist over the seed layer in the inter-level dielectric first regions;
depositing a first conductive material within the inter-level dielectric second region
trenches to form a plurality of conductive lines;
removing the resist;
depositing a MIMCap dielectric over the inter-level dielectric first region within the
first region trenches; and
depositing a second conductive material over the MIMCap dielectric within the
first region trenches to form a MIMCap top plate.
